

Fig.1 D/R of pulse-CVD a-SiC

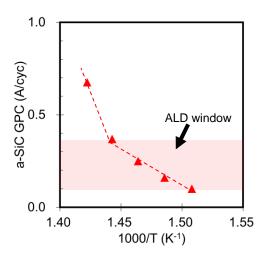
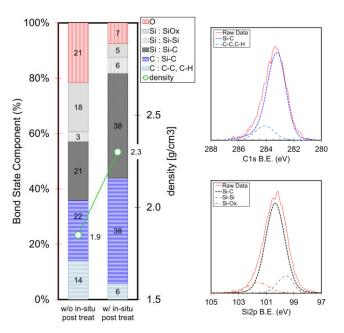


Fig.3 GPC of ALD a-SiC as a function of temperature



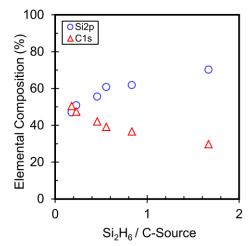


Fig.2 Si/C component ratio of CVD a-SiC film as a function of gas ratio of silicon source to carbon source

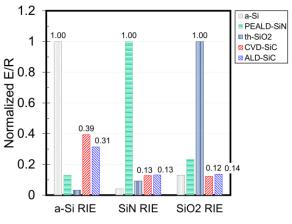


Fig.5 Dry etching rate selectivity of CVD/ALD-SiC in several RIE conditions

Fig.4 Bond state distribution and film density of ALD a-SiC with or without in-situ post treatment(left), deconvoluted C1s peaks(right top) and Si2p peaks(right bottom)